



# SRA2206E

PNP Silicon Transistor

## Descriptions

- Switching application
- Interface circuit and driver circuit application

## Features

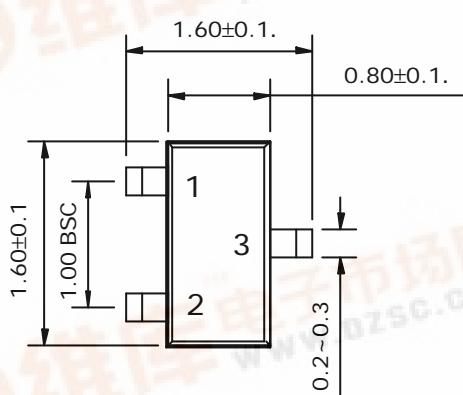
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- High packing density

## Ordering Information

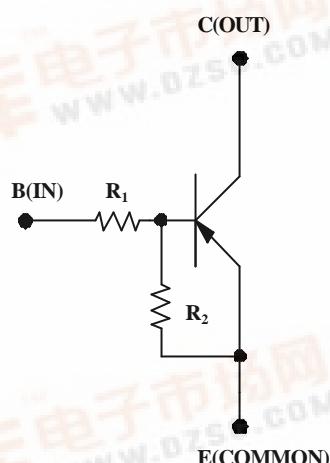
Type NO.	Marking	Package Code
SRA2206E	6R	SOT-523

## Outline Dimensions

unit : mm



### Equivalent Circuit



### PIN Connections

1. Base
2. Emitter
3. Collector

R <sub>1</sub>	R <sub>2</sub>
4.7kW	47kW

**Absolute maximum ratings**

(Ta=25°C)

Characteristic	Symbol	Ratings	Unit
Out Voltage	V <sub>O</sub>	-50	V
Input Voltage	V <sub>I</sub>	-20	V
Out Current	I <sub>O</sub>	-100	mA
Power Dissipation	P <sub>D</sub>	150	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ 150	°C

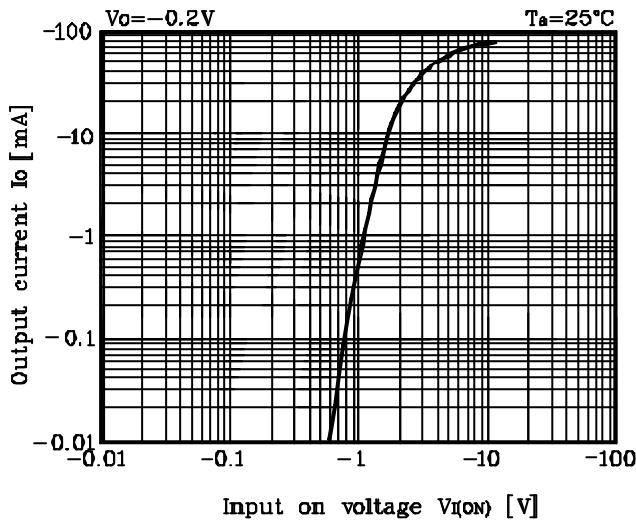
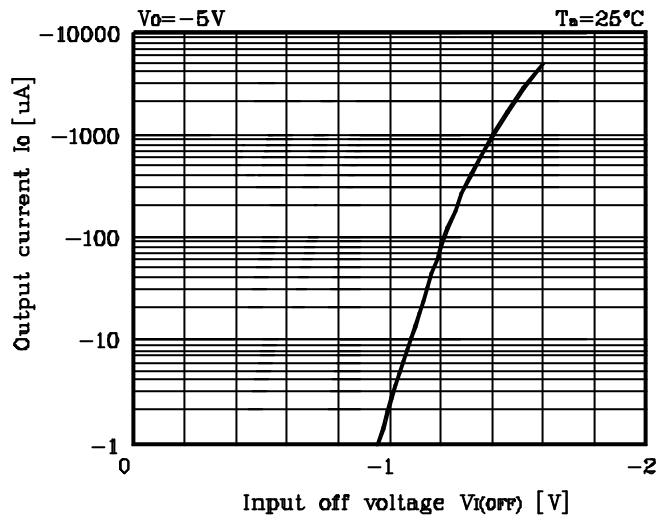
**Electrical Characteristics**

(Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Output Cut-off Current	I <sub>O(OFF)</sub>	V <sub>O</sub> =-50V, V <sub>I</sub> =0	-	-	-500	nA
DC Current Gain	G <sub>I</sub>	V <sub>O</sub> =-5V, I <sub>O</sub> =-10mA	80	200	-	-
Output Voltage	V <sub>O(ON)</sub>	I <sub>O</sub> =-10mA, I <sub>I</sub> =-0.5mA	-	-0.1	-0.3	V
Input Voltage (ON)	V <sub>I(ON)</sub>	V <sub>O</sub> =-0.2V, I <sub>O</sub> =-5mA	-	-0.9	-1.3	V
Input Voltage (OFF)	V <sub>I(OFF)</sub>	V <sub>O</sub> =-5V, I <sub>O</sub> =-0.1mA	-0.5	-0.65	-	V
Transition Frequency	f <sub>T</sub> *	V <sub>O</sub> =-10V, I <sub>O</sub> =-5mA	-	200	-	MHz
Input Current	I <sub>I</sub>	V <sub>I</sub> =-5V	-	-	-1.8	mA

\*: Characteristic of Transistor Only

## Electrical Characteristic Curves

**Fig. 1**  $I_o$  -  $V_{I(ON)}$ **Fig. 2**  $I_o$  -  $V_{I(OFF)}$ **Fig. 3**  $G_I$  -  $I_o$ 